

# MJE344

## Plastic NPN Silicon Medium-Power Transistor

This device is useful for medium voltage applications requiring high  $f_T$  such as converters and extended range amplifiers.

### Features

- Pb-Free Package is Available\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	200	Vdc
Collector-Base Voltage	$V_{CB}$	200	Vdc
Emitter Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current – Continuous	$I_C$	500	mAdc
Base Current	$I_B$	250	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	20 0.16	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	6.25	$^\circ\text{C/W}$

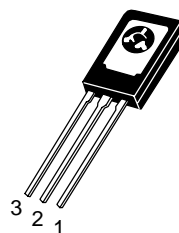
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



**ON Semiconductor**<sup>®</sup>

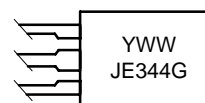
<http://onsemi.com>

**0.5 AMPERE  
POWER TRANSISTORS  
NPN SILICON  
150–200 VOLTS, 20 WATTS**



**TO-225  
CASE 77  
STYLE 1**

### MARKING DIAGRAM



Y = Year  
WW = Work Week  
JE344 = Device Code  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping
MJE344	TO-225	500 Units/Box
MJE344G	TO-225 (Pb-Free)	500 Units/Box

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJE344

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage ( $I_C = 1.0\text{ mAdc}$ , $I_B = 0$ )	$V_{CEO(sus)}$	200	–	Vdc
Collector Cutoff Current ( $V_{CE} = 200\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	–	1.0	mAdc
Collector Cutoff Current ( $V_{CB} = 200\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	0.1	mAdc
Emitter Cutoff Current ( $V_{EB} = 5.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	0.1	mAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ )	$h_{FE}$	30	300	–
Collector–Emitter Saturation Voltage ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{CE(sat)}$	–	1.0	Vdc
Base–Emitter On Voltage ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ )	$V_{BE(on)}$	–	1.0	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 25\text{ Vdc}$ , $f = 10\text{ MHz}$ )	$f_T$	15	–	MHz
Output Capacitance ( $V_{CB} = 20\text{ Vdc}$ , $I_E = 0$ , $f = 100\text{ kHz}$ )	$C_{ob}$	–	15	pF
Small–Signal Current Gain ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	25	–	–

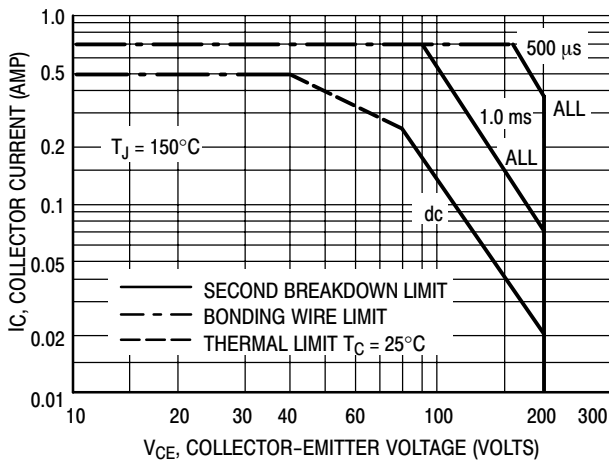


Figure 1. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

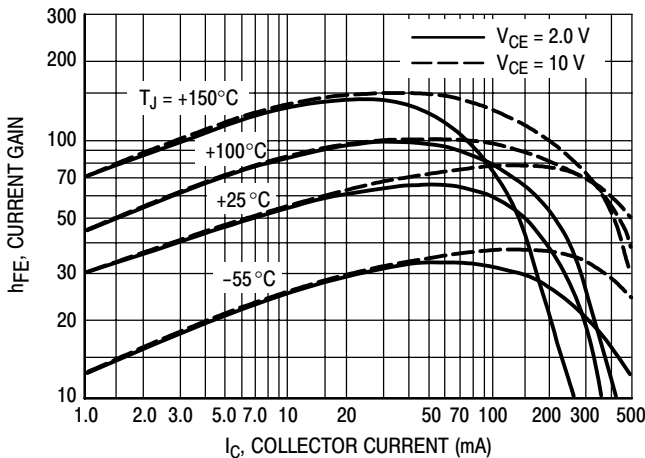


Figure 2. DC Current Gain

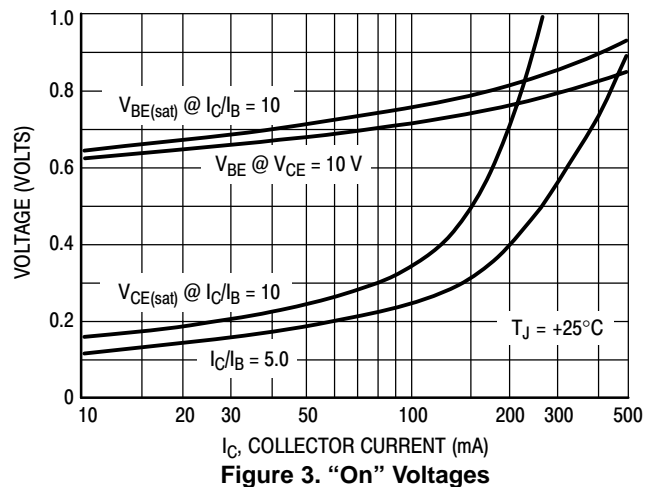
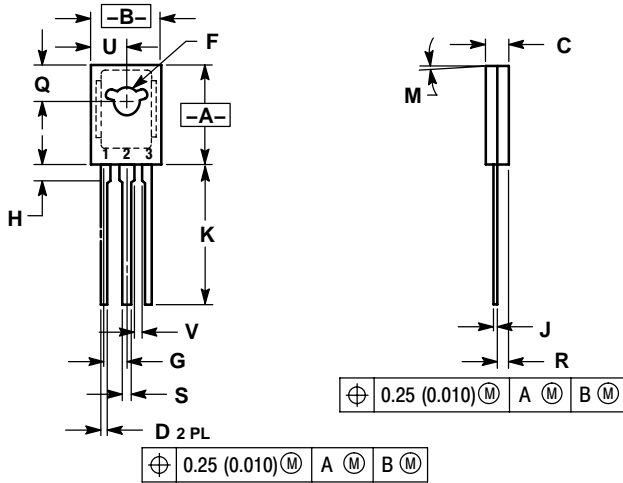


Figure 3. "On" Voltages

# MJE344

## PACKAGE DIMENSIONS

TO-225  
CASE 77-09  
ISSUE Z



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

### STYLE 1:

1. EMITTER
2. COLLECTOR
3. BASE

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